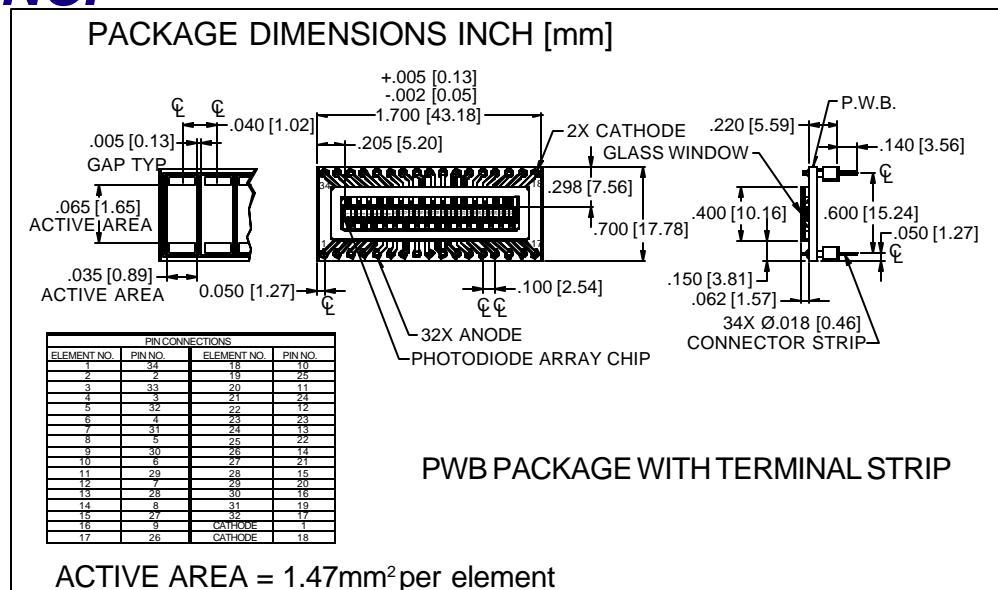
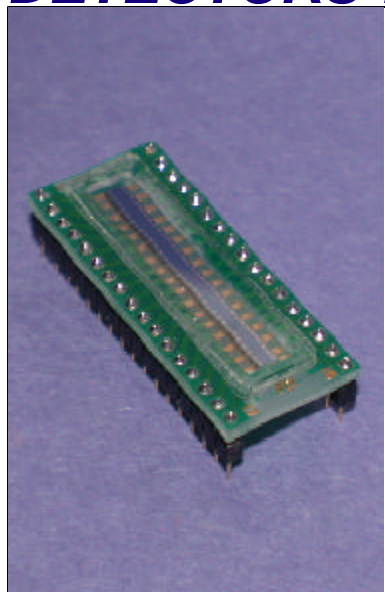


PHOTONIC DETECTORS INC.

Silicon Photodiode Array, Photoconductive 32 Element Type PDB-C232



FEATURES

- .100 inch centers
- Uniform outputs ($\pm 5\%$)
- Blue enhanced
- Low crosstalk ($\pm 2\%$)

DESCRIPTION

The **PDB-C232** is a common cathode, monolithic silicon PIN photodiode linear array. Packaged on a custom P.C.B. substrate, with dual .100 inch center terminal strips.

APPLICATIONS

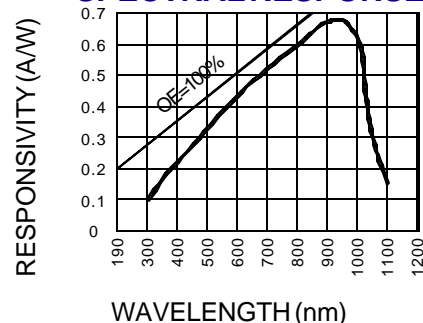
- Card reader
- Scanners
- Character recognition

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V_{BR}	Reverse Voltage		50	V
T_{STG}	Storage Temperature	-50	+100	°C
T_O	Operating Temperature Range	-40	+75	°C
T_S	Soldering Temperature*		+265	°C
I_L	Light Current		0.5	mA

*1/16 inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{SC}	Short Circuit Current	H = 100 fc, 2850 K	7.5	11		μA
I_D	Dark Current	H = 0, $V_R = 5 V$		100	150	pA
R_{SH}	Shunt Resistance	H = 0, $V_R = 10 mV$	100	250		MΩ
TCR_{SH}	RSH Temp. Coefficient	H = 0, $V_R = 10 mV$		-8		% / °C
C_J	Junction Capacitance	H = 0, $V_R = 0 V^{**}$		30		pF
λ_{range}	Spectral Application Range	Spot Scan	350		1100	nm
λ_p	Spectral Response - Peak	Spot Scan		950		nm
V_{BR}	Breakdown Voltage	I = 10 μA	30	75		V
NEP	Noise Equivalent Power	$V_R = 10 V$ @ Peak		1×10^{-14}		W / \sqrt{Hz}
tr	Response Time	RL = 50 Ω $V_R = 10 V$		200		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f = 1 MHz [FORM NO. 100-PDB-C232 REV B]